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#### What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

## Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

#### Details

E·XFI

Product Status	Active
Core Processor	ARM® Cortex®-M0
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	I <sup>2</sup> C, IrDA, LINbus, Microwire, SmartCard, SPI, SSP, UART/USART
Peripherals	Brown-out Detect/Reset, Cap Sense, LCD, LVD, POR, PWM, SmartSense, WDT
Number of I/O	55
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	8K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 5.5V
Data Converters	-
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	68-VFQFN Exposed Pad
Supplier Device Package	68-QFN (8x8)
Purchase URL	https://www.e-xfl.com/product-detail/infineon-technologies/cy8c4246lti-dm405

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong



## **More Information**

Cypress provides a wealth of data at www.cypress.com to help you to select the right PSoC device for your design, and to help you to quickly and effectively integrate the device into your design. For a comprehensive list of resources, see the knowledge base article KBA86521, How to Design with PSoC 3, PSoC 4, and PSoC 5LP. Following is an abbreviated list for PSoC 4:

- Overview: PSoC Portfolio, PSoC Roadmap
- Product Selectors: PSoC 1, PSoC 3, PSoC 4, PSoC 5LP In addition, PSoC Creator includes a device selection tool.
- Application notes: Cypress offers a large number of PSoC application notes covering a broad range of topics, from basic to advanced level. Recommended application notes for getting started with PSoC 4 are:
  - □ AN79953: Getting Started With PSoC 4
  - □ AN88619: PSoC 4 Hardware Design Considerations
  - □ AN86439: Using PSoC 4 GPIO Pins

PSoC Creator

- □ AN57821: Mixed Signal Circuit Board Layout
- □ AN81623: Digital Design Best Practices
- □ AN73854: Introduction To Bootloaders
- □ AN89610: ARM Cortex Code Optimization

- Technical Reference Manual (TRM) is in two documents:
- □ Architecture TRM details each PSoC 4 functional block.
- □ Registers TRM describes each of the PSoC 4 registers.
- Development Kits:
  - CY8CKIT-042, PSoC 4 Pioneer Kit, is an easy-to-use and inexpensive development platform. This kit includes connectors for Arduino<sup>™</sup> compatible shields and Digilent® Pmod<sup>™</sup> daughter cards.
  - CY8CKIT-049 is a very low-cost prototyping platform. It is a low-cost alternative to sampling PSoC 4 devices.
  - CY8CKIT-001 is a common development platform for any one of the PSoC 1, PSoC 3, PSoC 4, or PSoC 5LP families of devices.

The MiniProg3 device provides an interface for flash programming and debug.

PSoC Creator is a free Windows-based Integrated Design Environment (IDE). It enables concurrent hardware and firmware design of PSoC 3, PSoC 4, and PSoC 5LP based systems. Create designs using classic, familiar schematic capture supported by over 100 pre-verified, production-ready PSoC Components; see the list of component datasheets. With PSoC Creator, you can:

- 1. Drag and drop component icons to build your hardware system design in the main design workspace
- 2. Codesign your application firmware with the PSoC hardware, using the PSoC Creator IDE C compiler
- 3. Configure components using the configuration tools
- 4. Explore the library of 100+ components
- 5. Review component datasheets

## Figure 1. Multiple-Sensor Example Project in PSoC Creator





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# PSoC 4200M Block Diagram



The PSoC 4200-M devices include extensive support for programming, testing, debugging, and tracing both hardware and firmware.

The ARM Serial\_Wire Debug (SWD) interface supports all programming and debug features of the device.

Complete debug-on-chip functionality enables full-device debugging in the final system using the standard production device. It does not require special interfaces, debugging pods, simulators, or emulators. Only the standard programming connections are required to fully support debug.

The PSoC Creator Integrated Development Environment (IDE) provides fully integrated programming and debug support for PSoC 4200-M devices. The SWD interface is fully compatible with industry-standard third-party tools. The PSoC 4200-M family provides a level of security not possible with multi-chip application solutions or with microcontrollers. This is due to its ability to disable debug features, robust flash protection, and because it allows customer-proprietary functionality to be implemented in on-chip programmable blocks.

The debug circuits are enabled by default and can only be disabled in firmware. If not enabled, the only way to re-enable them is to erase the entire device, clear flash protection, and reprogram the device with new firmware that enables debugging.

Additionally, all device interfaces can be permanently disabled (device security) for applications concerned about phishing attacks due to a maliciously reprogrammed device or attempts to defeat security by starting and interrupting flash programming sequences. Because all programming, debug, and test interfaces are disabled when maximum device security is enabled, PSoC 4200-M with device security enabled may not be returned for failure analysis. This is a trade-off the PSoC 4200-M allows the customer to make.



#### Watchdog Timer

A watchdog timer is implemented in the clock block running from the low-frequency clock; this allows watchdog operation during Deep Sleep and generates a watchdog reset or an interrupt if not serviced before the timeout occurs. The watchdog reset is recorded in the Reset Cause register.

#### Reset

The PSoC 4200M can be reset from a variety of sources including a software reset. Reset events are asynchronous and guarantee reversion to a known state. The reset cause is recorded in a register, which is sticky through reset and allows software to determine the cause of the reset. An XRES pin is reserved for external reset to avoid complications with configuration and multiple pin functions during power-on or reconfiguration.

#### Voltage Reference

The PSoC 4200M reference system generates all internally required references. A 1% voltage reference spec is provided for the 12-bit ADC. To allow better signal-to-noise ratios (SNR) and better absolute accuracy, it is possible to add an external bypass capacitor to the internal reference using a GPIO pin or to use an external reference for the SAR.

## Analog Blocks

#### 12-bit SAR ADC

The 12-bit 1 MSample/second SAR ADC can operate at a maximum clock rate of 18 MHz and requires a minimum of 18 clocks at that frequency to do a 12-bit conversion.

The block functionality is augmented for the user by adding a reference buffer to it (trimmable to  $\pm$ 1%) and by providing the choice of three internal voltage references: V<sub>DD</sub>, V<sub>DD</sub>/2, and

V<sub>REF</sub> (nominally 1.024 V) as well as an external reference through a GPIO pin. The Sample-and-Hold (S/H) aperture is programmable allowing the gain bandwidth requirements of the amplifier driving the SAR inputs, which determine its settling time, to be relaxed if required. The system performance will be 65 dB for true 12-bit precision if appropriate references are used and system noise levels permit. To improve performance in noisy conditions, it is possible to provide an external bypass (through a fixed pin location) for the internal reference amplifier.

The SAR is connected to a fixed set of pins through an 8-input sequencer (expandable to 16 inputs). The sequencer cycles through selected channels autonomously (sequencer scan) and does so with zero switching overhead (that is, the aggregate sampling bandwidth is equal to 1 Msps, whether it is for a single channel or distributed over several channels). The sequencer switching is effected through a state machine or through firmware-driven switching. A feature provided by the sequencer is buffering of each channel to reduce CPU interrupt service requirements. To accommodate signals with varying source impedance and frequency, it is possible to have different sample times programmable for each channel. In addition, the signal range specification through a pair of range registers (low and high range values) is implemented with a corresponding out-of-range interrupt if the digitized value exceeds the programmed range; this allows fast detection of out-of-range values without the necessity of having to wait for a sequencer scan to be completed and the CPU to read the values and check for out-of-range values in software.

The SAR is able to digitize the output of the on-board temperature sensor for calibration and other temperature-dependent functions. The SAR is not available in Deep Sleep and Hibernate modes as it requires a high-speed clock (up to 18 MHz). The SAR operating range is 1.71 to 5.5 V.

#### Figure 3. SAR ADC System Diagram





## GPIO

The PSoC 4200M has 55 GPIOs in the 68-pin QFN package. The GPIO block implements the following:

- Eight drive strength modes including strong push-pull, resistive pull-up and pull-down, weak (resistive) pull-up and pull-down, open drain and open source, input only, and disabled
- Input threshold select (CMOS or LVTTL)
- Individual control of input and output disables
- Hold mode for latching previous state (used for retaining I/O state in Deep Sleep mode and Hibernate modes)
- Selectable slew rates for dV/dt related noise control to improve EMI

The pins are organized in logical entities called ports, which are 8-bit in width. During power-on and reset, the blocks are forced to the disable state so as not to crowbar any inputs and/or cause excess turn-on current. A multiplexing network known as a high-speed I/O matrix is used to multiplex between various signals that may connect to an I/O pin. Pin locations for fixed-function peripherals are also fixed to reduce internal multiplexing complexity (these signals do not go through the DSI network). DSI signals are not affected by this and any pin on Ports 0, 1, 2, and 3 may be routed to any UDB through the DSI network. Only pins on Ports 0, 1, 2, and 3 may be routed through DSI signals.

Data output and pin state registers store, respectively, the values to be driven on the pins and the states of the pins themselves.

Every I/O pin can generate an interrupt if so enabled and each I/O port has an interrupt request (IRQ) and interrupt service routine (ISR) vector associated with it (8 for PSoC 4200M).

The Pins of Port 6 (up to 6 depending on the package) are overvoltage tolerant (V<sub>IN</sub> can exceed V<sub>DD</sub>). The overvoltage cells will not sink more than 10  $\mu$ A when their inputs exceed V<sub>DDIO</sub> in compliance with I<sup>2</sup>C specifications.

#### **Special Function Peripherals**

#### LCD Segment Drive

The PSoC 4200M has an LCD controller, which can drive up to four commons and up to 51 segments. Any pin can be either a common or a segment pin. It uses full digital methods to drive the LCD segments requiring no generation of internal LCD voltages.

The two methods used are referred to as digital correlation and PWM.

Digital correlation pertains to modulating the frequency and levels of the common and segment signals to generate the highest RMS voltage across a segment to light it up or to keep the RMS signal zero. This method is good for STN displays but may result in reduced contrast with TN (cheaper) displays.

PWM pertains to driving the panel with PWM signals to effectively use the capacitance of the panel to provide the integration of the modulated pulse-width to generate the desired LCD voltage. This method results in higher power consumption but can result in better results when driving TN displays. LCD operation is supported during Deep Sleep refreshing a small display buffer (4 bits; 1 32-bit register per port).

#### CapSense

CapSense is supported on all pins in the PSoC 4200M through a CapSense Sigma-Delta (CSD) block that can be connected to any pin through an analog mux bus that any GPIO pin can be connected to via an Analog switch. CapSense functionality can thus be provided on any pin or group of pins in a system under software control. A component is provided for the CapSense block, which provides automatic hardware tuning (Cypress SmartSense<sup>™</sup>), to make it easy for the user.

Shield voltage can be driven on another Mux Bus to provide water tolerance capability. Water tolerance is provided by driving the shield electrode in phase with the sense electrode to keep the shield capacitance from attenuating the sensed input.

Each CSD block has two IDACs which can be used for general purposes if CapSense is not being used.(both IDACs are available in that case) or if CapSense is used without water tolerance (one IDAC is available). The PSoC 4200M has two CSD blocks which can be used independently; one for CapSense and one providing two IDACs.

The two CapSense blocks are referred to as CSD0 and CSD1. Capacitance sensing inputs on Ports 0, 1, 2, 3, 4, 6, and 7 are sensed by CSD0. Capacitance sensing inputs on Port 5 are sensed by CSD1.



Each of the pins shown in the previous table can have multiple programmable functions as shown in the following table. Column headings refer to Analog and Alternate pin functions.:

Port/Pin	Analog	Alt. Function 1	Alt. Function 2	Alt. Function 3	Alt. Function 4	Alt. Function 5
P0.0	lpcomp.in_p[0]			can[1].can_rx:0		scb[0].spi_select1:0
P0.1	lpcomp.in_n[0]			can[1].can_tx:0		scb[0].spi_select2:0
P0.2	lpcomp.in_p[1]					scb[0].spi_select3:0
P0.3	lpcomp.in_n[1]					
P0.4	wco_in		scb[1].uart_rx:0		scb[1].i2c_scl:0	scb[1].spi_mosi:1
P0.5	wco_out		scb[1].uart_tx:0		scb[1].i2c_sda:0	scb[1].spi_miso:1
P0.6		ext_clk:0	scb[1].uart_cts:0			scb[1].spi_clk:1
P0.7			scb[1].uart_rts:0	can[1].can_tx_enb_n:0	wakeup	scb[1].spi_select0:1
P5.0	ctb1.oa0.inp	tcpwm.line[4]:2	scb[2].uart_rx:0		scb[2].i2c_scl:0	scb[2].spi_mosi:0
P5.1	ctb1.oa0.inm	tcpwm.line_compl[4]:2	scb[2].uart_tx:0		scb[2].i2c_sda:0	scb[2].spi_miso:0
P5.2	ctb1.oa0.out	tcpwm.line[5]:2	scb[2].uart_cts:0		lpcomp.comp[0]:1	scb[2].spi_clk:0
P5.3	ctb1.oa1.out	tcpwm.line_compl[5]:2	scb[2].uart_rts:0		lpcomp.comp[1]:1	scb[2].spi_select0:0
P5.4	ctb1.oa1.inm	tcpwm.line[6]:2				scb[2].spi_select1:0
P5.5	ctb1.oa1.inp	tcpwm.line_compl[6]:2				scb[2].spi_select2:0
P5.6	ctb1.oa0.inp_alt	tcpwm.line[7]:0				scb[2].spi_select3:0
P5.7	ctb1.oa1.inp_alt	tcpwm.line_compl[7]:0				
P1.0	ctb0.oa0.inp	tcpwm.line[2]:1	scb[0].uart_rx:1		scb[0].i2c_scl:0	scb[0].spi_mosi:1
P1.1	ctb0.oa0.inm	tcpwm.line_compl[2]:1	scb[0].uart_tx:1		scb[0].i2c_sda:0	scb[0].spi_miso:1
P1.2	ctb0.oa0.out	tcpwm.line[3]:1	scb[0].uart_cts:1			scb[0].spi_clk:1
P1.3	ctb0.oa1.out	tcpwm.line_compl[3]:1	scb[0].uart_rts:1			scb[0].spi_select0:1
P1.4	ctb0.oa1.inm	tcpwm.line[6]:1				scb[0].spi_select1:1
P1.5	ctb0.oa1.inp	tcpwm.line_compl[6]:1				scb[0].spi_select2:1
P1.6	ctb0.oa0.inp_alt	tcpwm.line[7]:1				scb[0].spi_select3:1
P1.7	ctb0.oa1.inp_alt	tcpwm.line_compl[7]:1				
P2.0	sarmux.0	tcpwm.line[4]:1			scb[1].i2c_scl:1	scb[1].spi_mosi:2
P2.1	sarmux.1	tcpwm.line_compl[4]:1			scb[1].i2c_sda:1	scb[1].spi_miso:2
P2.2	sarmux.2	tcpwm.line[5]:1				scb[1].spi_clk:2
P2.3	sarmux.3	tcpwm.line_compl[5]:1				scb[1].spi_select0:2
P2.4	sarmux.4	tcpwm.line[0]:1				scb[1].spi_select1:1
P2.5	sarmux.5	tcpwm.line_compl[0]:1				scb[1].spi_select2:1
P2.6	sarmux.6	tcpwm.line[1]:1				scb[1].spi_select3:1



## Power

The supply voltage range is 1.71 to 5.5 V with all functions and circuits operating over that range.

The PSoC 4200M family allows two distinct modes of power supply operation: Unregulated External Supply and Regulated External Supply modes.

## Unregulated External Supply

In this mode, the PSoC 4200M is powered by an External Power Supply that can be anywhere in the range of 1.8 to 5.5 V. This range is also designed for battery-powered operation, for instance, the chip can be powered from a battery system that starts at 3.5V and works down to 1.8 V. In this mode, the internal regulator of the PSoC 4200M supplies the internal logic and the VCCD output of the PSoC 4200M must be bypassed to ground via an external Capacitor (in the range of 1 to 1.6  $\mu$ F; X5R ceramic or better).

The grounds, VSSA and VSS, must be shorted together. Bypass capacitors must be used from VDDD and VDDA to ground, typical practice for systems in this frequency range is to use a capacitor in the 1  $\mu$ F range in parallel with a smaller capacitor (0.1  $\mu$ F, for example). Note that these are simply rules of thumb and that, for critical applications, the PCB layout, lead inductance, and the Bypass capacitor parasitic should be simulated to design and obtain optimal bypassing.

Power Supply	Bypass Capacitors
VDDD–VSS and VDDIO-VSS	0.1 $\mu$ F ceramic at each pin plus bulk capacitor 1 to 10 $\mu$ F.
VDDA-VSSA	0.1 $\mu$ F ceramic at pin. Additional 1 $\mu$ F to 10 $\mu$ F bulk capacitor
VCCD-VSS	1 $\mu$ F ceramic capacitor at the VCCD pin
VREF–VSSA (optional)	The internal bandgap may be bypassed with a 1 $\mu$ F to 10 $\mu$ F capacitor for better ADC performance.

## **Regulated External Supply**

In this mode, the PSoC 4200M is powered by an external power supply that must be within the range of 1.71 to 1.89 V (1.8  $\pm$ 5%); note that this range needs to include power supply ripple. VCCD and VDDD pins are shorted together and bypassed. The internal regulator is disabled in firmware.



# **Electrical Specifications**

## **Absolute Maximum Ratings**

## Table 1. Absolute Maximum Ratings<sup>[1]</sup>

Spec ID#	Parameter	Description	Min	Тур	Мах	Units	Details/Conditions
SID1	V <sub>DD_ABS</sub>	Analog or digital supply relative to $V_{SS}$ ( $V_{SSD} = V_{SSA}$ )	-0.5	-	6	V	Absolute maximum
SID2	V <sub>CCD_ABS</sub>	Direct digital core voltage input relative to $V_{\mbox{\scriptsize SSD}}$	-0.5	-	1.95	V	Absolute maximum
SID3	V <sub>GPIO_ABS</sub>	GPIO voltage; V <sub>DDD</sub> or V <sub>DDA</sub>	-0.5	-	V <sub>DD</sub> +0.5	V	Absolute maximum
SID4	I <sub>GPIO_ABS</sub>	Current per GPIO	-25	-	25	mA	Absolute maximum
SID5	I <sub>G-PIO_injection</sub>	GPIO injection current per pin	-0.5	-	0.5	mA	Absolute maximum
BID44	ESD_HBM	Electrostatic discharge human body model	2200	-	-	V	
BID45	ESD_CDM	Electrostatic discharge charged device model	500	-	-	V	
BID46	LU	Pin current for latch-up	-140	_	140	mA	

## **Device Level Specifications**

All specifications are valid for -40 °C  $\leq$  TA  $\leq$  105 °C and TJ  $\leq$  125 °C, except where noted. Specifications are valid for 1.71 V to 5.5 V, except where noted.

#### Table 2. DC Specifications

Spec ID#	Parameter	Description	Min	Тур	Max	Units	Details / Conditions
SID53	V <sub>DD</sub>	Power Supply Input Voltage (V <sub>DDA</sub> = V <sub>DDD</sub> = V <sub>DD</sub> )	1.8	-	5.5	V	With regulator enabled
SID255	V <sub>DDD</sub>	Power Supply Input Voltage unregulated	1.71	1.8	1.89	V	Internally unregulated Supply
SID54	V <sub>CCD</sub>	Output voltage (for core logic)	-	1.8	-	V	
SID55	C <sub>EFC</sub>	External Regulator voltage bypass	1	1.3	1.6	μF	X5R ceramic or better
SID56	C <sub>EXC</sub>	Power supply decoupling capacitor	-	1	-	μF	X5R ceramic or better
Active Mod	de, V <sub>DD</sub> = 1.71 V te	o 5.5 V, −40 °C to +105 °C					•
SID6	I <sub>DD1</sub>	Execute from Flash; CPU at 6 MHz	-	2.2	2.8	mA	
SID7	I <sub>DD2</sub>	Execute from Flash; CPU at 12 MHz	-	3.7	4.2	mA	
SID8	I <sub>DD3</sub>	Execute from Flash; CPU at 24 MHz	-	6.7	7.2	mA	
SID9	I <sub>DD4</sub>	Execute from Flash; CPU at 48 MHz	-	13	13.8	mA	
Sleep Mod	e, –40 °C to +105	°C					
SID21	I <sub>DD16</sub>	I <sup>2</sup> C wakeup, WDT, and Comparators on. Regulator Off.	_	1.75	2.1	mA	V <sub>DD</sub> = 1.71 to 1.89, 6 MHz
SID22	I <sub>DD17</sub>	I <sup>2</sup> C wakeup, WDT, and Comparators on.	-	1.7	2.1	mA	V <sub>DD</sub> = 1.8 to 5.5, 6 MHz
SID23	I <sub>DD18</sub>	I <sup>2</sup> C wakeup, WDT, and Comparators on. Regulator Off.	-	2.35	2.8	mA	V <sub>DD</sub> = 1.71 to 1.89, 12 MHz
SID24	I <sub>DD19</sub>	I <sup>2</sup> C wakeup, WDT, and Comparators on.	_	2.25	2.8	mA	V <sub>DD</sub> = 1.8 to 5.5, 12 MHz

#### Note

Usage above the absolute maximum conditions listed in Table 1 may cause permanent damage to the device. Exposure to absolute maximum conditions for extended periods of time may affect device reliability. The maximum storage temperature is 150 °C in compliance with JEDEC Standard JESD22-A103, High Temperature Storage Life. When used below absolute maximum conditions but above normal operating conditions, the device may not operate to specification.



## Table 2. DC Specifications (continued)

Spec ID#	Parameter	Description	Min	Тур	Max	Units	Details / Conditions
Deep Sleep	Mode, –40 °C to	+ 60 °C					
SID30	I <sub>DD25</sub>	I <sup>2</sup> C wakeup and WDT on. Regulator Off.	-	1.55	20	μA	V <sub>DD</sub> = 1.71 to 1.89
SID31	I <sub>DD26</sub>	I <sup>2</sup> C wakeup and WDT on.	-	1.35	15	μA	V <sub>DD</sub> = 1.8 to 3.6
SID32	I <sub>DD27</sub>	I <sup>2</sup> C wakeup and WDT on.	-	1.5	15	μA	V <sub>DD</sub> = 3.6 to 5.5
Deep Sleep	Mode, +85 °C	· · · · · · · · · · · · · · · · · · ·					
SID33	I <sub>DD28</sub>	I <sup>2</sup> C wakeup and WDT on. Regulator Off.	-	-	60	μA	V <sub>DD</sub> = 1.71 to 1.89
SID34	I <sub>DD29</sub>	I <sup>2</sup> C wakeup and WDT on.	_	-	45	μA	V <sub>DD</sub> = 1.8 to 3.6
SID35	I <sub>DD30</sub>	I <sup>2</sup> C wakeup and WDT on.	-	-	30	μA	V <sub>DD</sub> = 3.6 to 5.5
Deep Sleep	o Mode, +105 °C	· · · · · · · · · · · · · · · · · · ·					
SID33Q	I <sub>DD28Q</sub>	I <sup>2</sup> C wakeup and WDT on. Regulator Off.	_	-	135	μA	V <sub>DD</sub> = 1.71 to 1.89
SID34Q	I <sub>DD29Q</sub>	I <sup>2</sup> C wakeup and WDT on.	-	-	180	μA	V <sub>DD</sub> = 1.8 to 3.6
SID35Q	I <sub>DD30Q</sub>	I <sup>2</sup> C wakeup and WDT on.	-	-	140	μA	V <sub>DD</sub> = 3.6 to 5.5
Hibernate	Mode, -40 °C to +	- 60 °C			•		
SID39	I <sub>DD34</sub>	Regulator Off.	-	150	3000	nA	V <sub>DD</sub> = 1.71 to 1.89
SID40	I <sub>DD35</sub>		_	150	1000	nA	V <sub>DD</sub> = 1.8 to 3.6
SID41	I <sub>DD36</sub>		_	150	1100	nA	V <sub>DD</sub> = 3.6 to 5.5
Hibernate	Mode, +85 °C						
SID42	I <sub>DD37</sub>	Regulator Off.	-	_	4500	nA	V <sub>DD</sub> = 1.71 to 1.89
SID43	I <sub>DD38</sub>		-	-	3500	nA	V <sub>DD</sub> = 1.8 to 3.6
SID44	I <sub>DD39</sub>		-	-	3500	nA	V <sub>DD</sub> = 3.6 to 5.5
Hibernate	Mode, +105 °C						
SID42Q	I <sub>DD37Q</sub>	Regulator Off.	-	1	19.4	μA	V <sub>DD</sub> = 1.71 to 1.89
SID43Q	I <sub>DD38Q</sub>		-	-	17	μA	V <sub>DD</sub> = 1.8 to 3.6
SID44Q	I <sub>DD39Q</sub>		-	-	16	μA	V <sub>DD</sub> = 3.6 to 5.5
Stop Mode							
SID304	I <sub>DD43A</sub>	Stop Mode current; $V_{DD}$ = 3.6 V	-	35	85	nA	T = -40 °C to +60 °C
SID304A	I <sub>DD43B</sub>	Stop Mode current; $V_{DD}$ = 3.6 V	_	-	1450	nA	T = +85 °C
Stop Mode	, +105 °C						
SID304Q	I <sub>DD43AQ</sub>	Stop Mode current; V <sub>DD</sub> = 3.6 V	-	-	5645	nA	
XRES curr	ent						
SID307	I <sub>DD_XR</sub>	Supply current while XRES asserted	_	2	5	mA	



## Table 4. GPIO DC Specifications (continued)

Spec ID#	Parameter	Description	Min	Тур	Max	Units	<b>Details/Conditions</b>
SID68	V <sub>HYSCMOS</sub>	Input hysteresis CMOS	0.05 × V <sub>DDD</sub>	-	-	mV	
SID69	IDIODE	Current through protection diode to $V_{DD}/Vss$	-	-	100	μA	Guaranteed by characterization
SID69A	I <sub>TOT_GPIO</sub>	Maximum Total Source or Sink Chip Current	-	-	200	mA	Guaranteed by characterization

## Table 5. GPIO AC Specifications

(Guaranteed by Characterization)<sup>[3]</sup>

Spec ID#	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
SID70	T <sub>RISEF</sub>	Rise time in fast strong mode	2	-	12	ns	3.3 V V <sub>DDD</sub> , Cload = 25 pF
SID71	T <sub>FALLF</sub>	Fall time in fast strong mode	2	-	12	ns	3.3 V V <sub>DDD</sub> , Cload = 25 pF
SID72	T <sub>RISES</sub>	Rise time in slow strong mode	10	-	60	ns	3.3 V V <sub>DDD</sub> , Cload = 25 pF
SID73	T <sub>FALLS</sub>	Fall time in slow strong mode	10	-	60	ns	3.3 V V <sub>DDD</sub> , Cload = 25 pF
SID74	F <sub>GPIOUT1</sub>	GPIO Fout;3.3 V $\leq$ V <sub>DDD</sub> $\leq$ 5.5 V. Fast strong mode.	_	-	33	MHz	90/10%, 25-pF load, 60/40 duty cycle
SID75	F <sub>GPIOUT2</sub>	GPIO Fout;1.7 V $\leq$ V <sub>DDD</sub> $\leq$ 3.3 V. Fast strong mode.	_	-	16.7	MHz	90/10%, 25-pF load, 60/40 duty cycle
SID76	F <sub>GPIOUT3</sub>	GPIO Fout;3.3 V $\leq$ V <sub>DDD</sub> $\leq$ 5.5 V. Slow strong mode.	_	-	7	MHz	90/10%, 25-pF load, 60/40 duty cycle
SID245	F <sub>GPIOUT4</sub>	GPIO Fout;1.7 V $\leq$ V <sub>DDD</sub> $\leq$ 3.3 V. Slow strong mode.	_	-	3.5	MHz	90/10%, 25-pF load, 60/40 duty cycle
SID246	F <sub>GPIOIN</sub>	GPIO input operating frequency; 1.71 V $\leq$ V <sub>DDD</sub> $\leq$ 5.5 V	_	-	48	MHz	90/10% V <sub>IO</sub>

## XRES

#### Table 6. XRES DC Specifications

Spec ID#	Parameter	Description	Min	Тур	Max	Units	Details/ Conditions
SID77	V <sub>IH</sub>	Input voltage high threshold	0.7 × V <sub>DDD</sub>	-	-	V	CMOS Input
SID78	V <sub>IL</sub>	Input voltage low threshold	-	-	0.3 × V <sub>DDD</sub>	V	CMOS Input
SID79	R <sub>PULLUP</sub>	Pull-up resistor	3.5	5.6	8.5	kΩ	
SID80	C <sub>IN</sub>	Input capacitance	-	3	-	pF	
SID81	V <sub>HYSXRES</sub>	Input voltage hysteresis	-	100	-	mV	Guaranteed by characterization
SID82	IDIODE	Current through protection diode to $V_{DDD}/V_{SS}$	_	-	100	μA	Guaranteed by characterization

#### Table 7. XRES AC Specifications

Spec ID#	Parameter	Description	Min	Тур	Max	Units	Details/ Conditions
SID83	T <sub>RESETWIDTH</sub>	Reset pulse width	1	_	_	μs	Guaranteed by characterization

Note

 Simultaneous switching transitions on many fully-loaded GPIO pins may cause ground perturbations depending on several factors including PCB and decoupling capacitor design. For applications that are very sensitive to ground perturbations, the slower GPIO slew rate setting may be used.



## Table 8. Opamp Specifications

(Guaranteed by Characterization) (continued)

Spec ID#	Parameter	Description	Min	Тур	Max	Units	Details/ Conditions
SID_DS_15	VOS_LOW_M1	Mode 1, Low current	_	5	-	mV	With trim 25 °C, 0.2 V to V <sub>DDA</sub> -1.5 V
SID_DS_16	VOS_HI_M2	Mode 2, High current	_	5	-	mV	With trim 25 °C, 0.2 V to V <sub>DDA</sub> -1.5 V
SID_DS_17	VOS_MED_M2	Mode 2, Medium current	-	5	-	mV	With trim 25 °C, 0.2 V to V <sub>DDA</sub> -1.5 V
SID_DS_18	VOS_LOW_M2	Mode 2, Low current	-	5	-	mV	With trim 25 °C, 0.2 V to V <sub>DDA</sub> -1.5 V
SID_DS_19	IOUT_HI_M1	Mode 1, High current	-	10	-	mA	Output is 0.5 V to V <sub>DDA</sub> -0.5 V
SID_DS_20	IOUT_MED_M1	Mode 1, Medium current	_	10	-	mA	Output is 0.5 V to V <sub>DDA</sub> -0.5 V
SID_DS_21	IOUT_LOW_M1	Mode 1, Low current	-	4	-	mA	Output is 0.5 V to V <sub>DDA</sub> -0.5 V
SID_DS_22	IOUT_HI_M2	Mode 2, High current	-	1	_	mA	Output is 0.5 V to V <sub>DDA</sub> -0.5 V
SID_DS_23	IOUT_MED_M2	Mode 2, Medium current	-	1	-	mA	Output is 0.5 V to V <sub>DDA</sub> -0.5 V
SID_DS_24	IOUT_LOW_M2	Mode 2, Low current	_	0.5	_	mA	Output is 0.5 V to V <sub>DDA</sub> -0.5 V

## Comparator

## Table 9. Comparator DC Specifications

Spec ID#	Parameter	Description	Min	Тур	Max	Units	Details/ Conditions
SID85	V <sub>OFFSET2</sub>	Input offset voltage, Common Mode voltage range from 0 to V <sub>DD</sub> -1	_	-	±4	mV	
SID85A	V <sub>OFFSET3</sub>	Input offset voltage. Ultra low-power mode ( $V_{DDD} \ge 2.2$ V for Temp < 0 °C, $V_{DDD} \ge 1.8$ V for Temp > 0 °C)	_	±12	-	mV	
SID86	V <sub>HYST</sub>	Hysteresis when enabled, Common Mode voltage range from 0 to V <sub>DD</sub> -1.	-	10	35	mV	Guaranteed by characterization
SID87	V <sub>ICM1</sub>	Input common mode voltage in normal mode	0	-	V <sub>DDD</sub> – 0.1	V	Modes 1 and 2.
SID247	V <sub>ICM2</sub>	Input common mode voltage in low power mode ( $V_{DDD} \ge 2.2 \text{ V}$ for Temp < 0 °C, $V_{DDD} \ge 1.8 \text{ V}$ for Temp > 0 °C)	0	-	V <sub>DDD</sub>	V	
SID247A	V <sub>ICM3</sub>	Input common mode voltage in ultra low power mode	0	-	V <sub>DDD</sub> – 1.15	V	
SID88	CMRR	Common mode rejection ratio	50	_	-	dB	$V_{DDD} \ge 2.7 V.$ Guaranteed by characterization
SID88A	CMRR	Common mode rejection ratio	42	_	-	dB	V <sub>DDD</sub> < 2.7 V. Guaranteed by characterization
SID89	I <sub>CMP1</sub>	Block current, normal mode	_	-	400	μA	Guaranteed by characterization



### Table 9. Comparator DC Specifications (continued)

Spec ID#	Parameter	Description	Min	Тур	Мах	Units	Details/ Conditions
SID248	I <sub>CMP2</sub>	Block current, low power mode	-	-	100	μA	Guaranteed by characterization
SID259	I <sub>CMP3</sub>	Block current, ultra low power mode ( $V_{DDD} \ge 2.2 \text{ V}$ for Temp < 0 °C, $V_{DDD} \ge$ 1.8 V for Temp > 0 °C)	-	6	28	μA	Guaranteed by characterization
SID90	Z <sub>CMP</sub>	DC input impedance of comparator	35	-	-	MΩ	Guaranteed by characterization

## Table 10. Comparator AC Specifications

(Guaranteed by Characterization)

Spec ID#	Parameter	Description	Min	Тур	Max	Units	<b>Details/Conditions</b>
SID91	T <sub>RESP1</sub>	Response time, normal mode	-	-	110	ns	50-mV overdrive
SID258	T <sub>RESP2</sub>	Response time, low power mode	-	-	200	ns	50-mV overdrive
SID92	T <sub>RESP3</sub>	Response time, ultra low power mode ( $V_{DDD} \ge 2.2 \text{ V}$ for Temp < 0 °C, $V_{DDD} \ge$ 1.8 V for Temp > 0 °C)	-	-	15	μs	200-mV overdrive

#### Temperature Sensor

## Table 11. Temperature Sensor Specifications

Spec ID#	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
SID93	T <sub>SENSACC</sub>	Temperature sensor accuracy	-5	±1	+5	°C	–40 to +85 °C

### SAR ADC

#### Table 12. SAR ADC DC Specifications

Spec ID#	Parameter	Description	Min	Тур	Max	Units	<b>Details/Conditions</b>
SID94	A_RES	Resolution	-	-	12	bits	
SID95	A_CHNIS_S	Number of channels - single ended	-	-	16		8 full speed
SID96	A-CHNKS_D	Number of channels - differential	_	-	8		Diff inputs use neighboring I/O
SID97	A-MONO	Monotonicity	-	-	-		Yes. Based on characterization
SID98	A_GAINERR	Gain error	-	-	±0.1	%	With external reference.
SID99	A_OFFSET	Input offset voltage	-	-	2	mV	Measured with 1-V V <sub>REF.</sub>
SID100	A_ISAR	Current consumption	-	-	1	mA	
SID101	A_VINS	Input voltage range - single ended	V <sub>SS</sub>	-	V <sub>DDA</sub>	V	Based on device characterization
SID102	A_VIND	Input voltage range - differential	V <sub>SS</sub>	-	V <sub>DDA</sub>	V	Based on device characterization
SID103	A_INRES	Input resistance	_	-	2.2	KΩ	Based on device characterization
SID104	A_INCAP	Input capacitance	_	-	10	pF	Based on device characterization



## Table 13. SAR ADC AC Specifications

(Guaranteed by Characterization)

Spec ID#	Parameter	Description	Min	Тур	Max	Units	<b>Details/Conditions</b>
SID106	A_PSRR	Power supply rejection ratio	70	-	-	dB	
SID107	A_CMRR	Common mode rejection ratio	66	-	-	dB	Measured at 1 V
SID108	A_SAMP_1	Sample rate with external reference bypass cap	-	-	1	Msps	
SID108A	A_SAMP_2	Sample rate with no bypass cap. Reference = $V_{DD}$	-	-	1	Msps	
SID108B	A_SAMP_3	Sample rate with no bypass cap. Internal reference	_	-	100	Ksps	
SID109	A_SNDR	Signal-to-noise and distortion ratio (SINAD)	66	-	-	dB	F <sub>IN</sub> = 10 kHz
SID111	A_INL	Integral non linearity	-1.4	-	+1.4	LSB	V <sub>DD</sub> = 1.71 to 5.5, 1 Msps, Vref = 1 to 5.5.
SID111A	A_INL	Integral non linearity	-1.4	-	+1.4	LSB	V <sub>DDD</sub> = 1.71 to 3.6, 1 Msps, Vref = 1.71 to V <sub>DDD</sub> .
SID111B	A_INL	Integral non linearity	-1.4	-	+1.4	LSB	V <sub>DDD</sub> = 1.71 to 5.5, 500 ksps, Vref = 1 to 5.5.
SID112	A_DNL	Differential non linearity	-0.9	-	+1.35	LSB	V <sub>DDD</sub> = 1.71 to 5.5, 1 Msps, Vref = 1 to 5.5.
SID112A	A_DNL	Differential non linearity	-0.9	-	+1.35	LSB	V <sub>DDD</sub> = 1.71 to 3.6, 1 Msps, Vref = 1.71 to V <sub>DDD</sub> .
SID112B	A_DNL	Differential non linearity	-0.9	-	+1.35	LSB	V <sub>DDD</sub> = 1.71 to 5.5, 500 ksps, Vref = 1 to 5.5.
SID113	A_THD	Total harmonic distortion	_	_	-65	dB	F <sub>IN</sub> = 10 kHz.

#### CSD

## Table 14. CSD Block Specification

Spec ID#	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
CSD Spec	ification						
SID308	VCSD	Voltage range of operation	1.71	_	5.5	V	
SID309	IDAC1	DNL for 8-bit resolution	-1	_	1	LSB	
SID310	IDAC1	INL for 8-bit resolution	-3	_	3	LSB	
SID311	IDAC2	DNL for 7-bit resolution	-1	_	1	LSB	
SID312	IDAC2	INL for 7-bit resolution	-3	_	3	LSB	
SID313	SNR	Ratio of counts of finger to noise. Guaranteed by characterization	5	-	_	Ratio	Capacitance range of 9 to 35 pF, 0.1-pF sensitivity
SID314	IDAC1_CRT1	Output current of Idac1 (8-bits) in High range	-	612	-	μA	
SID314A	IDAC1_CRT2	Output current of Idac1(8-bits) in Low range	-	306	-	μA	
SID315	IDAC2_CRT1	Output current of Idac2 (7-bits) in High range	-	304.8	-	μA	
SID315A	IDAC2_CRT2	Output current of Idac2 (7-bits) in Low range	_	152.4	_	μΑ	



## **Digital Peripherals**

The following specifications apply to the Timer/Counter/PWM peripheral in timer mode.

Timer/Counter/PWM

## Table 15. TCPWM Specifications

(Guaranteed by Characterization)

Spec ID	Parameter	Description	Min	Тур	Max	Units	<b>Details/Conditions</b>
SID.TCPWM.1	ITCPWM1	Block current consumption at 3 MHz	-	_	45	μA	All modes (Timer/Counter/PWM)
SID.TCPWM.2	ITCPWM2	Block current consumption at 12 MHz	_	-	155	μA	All modes (Timer/Counter/PWM)
SID.TCPWM.2A	ITCPWM3	Block current consumption at 48 MHz	_	_	650	μA	All modes (Timer/Counter/PWM)
SID.TCPWM.3	TCPWMFREQ	Operating frequency	_	-	Fc	MHz	Fc max = Fcpu. Maximum = 24 MHz
SID.TCPWM.4	TPWMENEXT	Input Trigger Pulse Width for all Trigger Events	2/Fc	-	_	ns	Trigger Events can be Stop, Start, Reload, Count, Capture, or Kill depending on which mode of operation is selected.
SID.TCPWM.5	TPWMEXT	Output Trigger Pulse widths	2/Fc	_	_	ns	Minimum possible width of Overflow, Underflow, and CC (Counter equals Compare value) trigger outputs
SID.TCPWM.5A	TCRES	Resolution of Counter	1/Fc	-	-	ns	Minimum time between successive counts
SID.TCPWM.5B	PWMRES	PWM Resolution	1/Fc	-	-	ns	Minimum pulse width of PWM Output
SID.TCPWM.5C	QRES	Quadrature inputs resolution	1/Fc	_	_	ns	Minimum pulse width between Quadrature phase inputs.

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## Table 16. Fixed I<sup>2</sup>C DC Specifications

(Guaranteed by Characterization)

Spec ID	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
SID149	I <sub>I2C1</sub>	Block current consumption at 100 kHz	-	-	50	μA	
SID150	I <sub>I2C2</sub>	Block current consumption at 400 kHz	-	-	135	μA	
SID151	I <sub>I2C3</sub>	Block current consumption at 1 Mbps	-	-	310	μA	
SID152	I <sub>I2C4</sub>	I <sup>2</sup> C enabled in Deep Sleep mode	_	_	1.4	μA	

## Table 17. Fixed I<sup>2</sup>C AC Specifications

(Guaranteed by Characterization)

Spec ID	Parameter	Description	Min	Тур	Max	Units	<b>Details/Conditions</b>
SID153	F <sub>I2C1</sub>	Bit rate	-	-	1	Mbps	



## Table 24. Fixed SPI Master mode AC Specifications

(Guaranteed by Characterization)

Spec ID	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
SID167	Т <sub>DMO</sub>	MOSI valid after Sclock driving edge	-	-	15	ns	
SID168	T <sub>DSI</sub>	MISO valid before Sclock capturing edge. Full clock, late MISO Sampling used	20	-	-	ns	
SID169	Т <sub>НМО</sub>	Previous MOSI data hold time with respect to capturing edge at Slave	0	_	-	ns	

## Table 25. Fixed SPI Slave mode AC Specifications

(Guaranteed by Characterization)

Spec ID	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
SID170	Т <sub>DMI</sub>	MOSI valid before Sclock capturing edge	40	-	-	ns	
SID171	T <sub>DSO</sub>	MISO valid after Sclock driving edge	-	-	42 + 3 × (1/FCPU)	ns	
SID171A	T <sub>DSO_ext</sub>	MISO valid after Sclock driving edge in Ext. Clock mode	-	-	48	ns	
SID172	T <sub>HSO</sub>	Previous MISO data hold time	0	-	-	ns	
SID172A	T <sub>SSELSCK</sub>	SSEL Valid to first SCK Valid edge	100	-	_	ns	

## Memory

## Table 26. Flash DC Specifications

Spec ID	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
SID173	V <sub>PE</sub>	Erase and program voltage	1.71	-	5.5	V	

## Table 27. Flash AC Specifications

Spec ID	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
SID174	T <sub>ROWWRITE</sub>	Row (block) write time (erase and program)	-	_	20	ms	Row (block) = 128 bytes
SID175	T <sub>ROWERASE</sub>	Row erase time	-	-	13	ms	
SID176	T <sub>ROWPROGRAM</sub>	Row program time after erase	-	-	7	ms	
SID178	T <sub>BULKERASE</sub>	Bulk erase time (128 KB)	-	_	35	ms	
SID179	T <sub>SECTORERASE</sub>	Sector erase time (8 KB)	-	-	15	ms	
SID180	T <sub>DEVPROG</sub>	Total device program time	_	_	15	seconds	Guaranteed by charac- terization
SID181	F <sub>END</sub>	Flash endurance	100 K	_	_	cycles	Guaranteed by charac- terization
SID182	F <sub>RET</sub>	Flash retention. $T_A \le 55 \degree$ C, 100 K P/E cycles	К 20 – –		_	years	Guaranteed by charac- terization
SID182A		Flash retention. $T_A \le 85$ °C, 10 K P/E cycles	10	_	_	years	Guaranteed by charac- terization
SID182B	F <sub>RETQ</sub>	Flash retention. $T_A \le 105$ °C, 10K P/E cycles, $\le$ three years at $T_A \ge$ 85 °C	10	20	-	years	Guaranteed by charac- terization.



## **System Resources**

Power-on-Reset (POR) with Brown Out

## Table 28. Imprecise Power On Reset (PRES)

Spec ID	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
SID185	V <sub>RISEIPOR</sub>	Rising trip voltage	0.80	-	1.45	V	Guaranteed by charac- terization
SID186	V <sub>FALLIPOR</sub>	Falling trip voltage	0.75	-	1.4	V	Guaranteed by charac- terization
SID187	V <sub>IPORHYST</sub>	Hysteresis	15	-	200	mV	Guaranteed by charac- terization

## Table 29. Precise Power On Reset (POR)

Spec ID	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
SID190	V <sub>FALLPPOR</sub>	BOD trip voltage in active and sleep modes	1.64	_	_	V	Guaranteed by charac- terization
SID192	V <sub>FALLDPSLP</sub>	BOD trip voltage in Deep Sleep	1.4	-	-	V	Guaranteed by charac- terization

## Voltage Monitors

#### Table 30. Voltage Monitors DC Specifications

Spec ID	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
SID195	V <sub>LVI1</sub>	LVI_A/D_SEL[3:0] = 0000b	1.71	1.75	1.79	V	
SID196	V <sub>LVI2</sub>	LVI_A/D_SEL[3:0] = 0001b	1.76	1.80	1.85	V	
SID197	V <sub>LVI3</sub>	LVI_A/D_SEL[3:0] = 0010b	1.85	1.90	1.95	V	
SID198	V <sub>LVI4</sub>	LVI_A/D_SEL[3:0] = 0011b	1.95	2.00	2.05	V	
SID199	V <sub>LVI5</sub>	LVI_A/D_SEL[3:0] = 0100b 2.05 2.10 2.15 V					
SID200	V <sub>LVI6</sub>	LVI_A/D_SEL[3:0] = 0101b	2.15	2.20	2.26	V	
SID201	V <sub>LVI7</sub>	LVI_A/D_SEL[3:0] = 0110b	2.24	2.30	2.36	V	
SID202	V <sub>LVI8</sub>	LVI_A/D_SEL[3:0] = 0111b	2.34	2.40	2.46	V	
SID203	V <sub>LVI9</sub>	LVI_A/D_SEL[3:0] = 1000b	2.44	2.50	2.56	V	
SID204	V <sub>LVI10</sub>	LVI_A/D_SEL[3:0] = 1001b	2.54	2.60	2.67	V	
SID205	V <sub>LVI11</sub>	LVI_A/D_SEL[3:0] = 1010b	2.63	2.70	2.77	V	
SID206	V <sub>LVI12</sub>	LVI_A/D_SEL[3:0] = 1011b	2.73	2.80	2.87	V	
SID207	V <sub>LVI13</sub>	LVI_A/D_SEL[3:0] = 1100b	2.83	2.90	2.97	V	
SID208	V <sub>LVI14</sub>	LVI_A/D_SEL[3:0] = 1101b	2.93	3.00	3.08	V	
SID209	V <sub>LVI15</sub>	LVI_A/D_SEL[3:0] = 1110b	3.12	3.20	3.28	V	
SID210	V <sub>LVI16</sub>	LVI_A/D_SEL[3:0] = 1111b	4.39	4.50	4.61	V	
SID211	LVI_IDD	Block current	_	_	100	μA	Guaranteed by charac- terization

## Table 31. Voltage Monitors AC Specifications

Spec ID	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
SID212	T <sub>MONTRIP</sub>	Voltage monitor trip time	1	-	1	μs	Guaranteed by charac- terization



## SWD Interface

## Table 32. SWD Interface Specifications

Spec ID	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
SID213	F_SWDCLK1	$3.3 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}$	-	-	14	MHz	SWDCLK ≤ 1/3 CPU clock frequency
SID214	F_SWDCLK2	$1.71~V \leq V_{DD} \leq 3.3~V$	-	-	7	MHz	SWDCLK ≤ 1/3 CPU clock frequency
SID215	T_SWDI_SETUP	T = 1/f SWDCLK	0.25*T	-	-	ns	Guaranteed by characterization
SID216	T_SWDI_HOLD	T = 1/f SWDCLK	0.25*T	-	-	ns	Guaranteed by characterization
SID217	T_SWDO_VALID	T = 1/f SWDCLK	-	-	0.5*T	ns	Guaranteed by characterization
SID217A	T_SWDO_HOLD	T = 1/f SWDCLK	1	-	_	ns	Guaranteed by characterization

Internal Main Oscillator

## Table 33. IMO DC Specifications

(Guaranteed by Design)

Spec ID	Parameter	Description Min Typ Max		Units	Details/Conditions		
SID218	I <sub>IMO1</sub>	IMO operating current at 48 MHz	_	-	1000	μA	
SID219	I <sub>IMO2</sub>	IMO operating current at 24 MHz	_	-	325	μA	
SID220	I <sub>IMO3</sub>	IMO operating current at 12 MHz	_	-	225	μA	
SID221	I <sub>IMO4</sub>	IMO operating current at 6 MHz	_	-	180	μA	
SID222	I <sub>IMO5</sub>	IMO operating current at 3 MHz	_	-	150	μΑ	

## Table 34. IMO AC Specifications

Spec ID	Parameter	meter Description		Тур	Max	Units	Details/Conditions
SID223	F <sub>IMOTOL1</sub>	Frequency variation from 3 to – – ±2 48 MHz		%	±3% if T <sub>A</sub> > 85 °C and IMO frequency < 24 MHz		
SID226	T <sub>STARTIMO</sub>	IMO startup time	-	-	12	μs	
SID227	T <sub>JITRMSIMO1</sub>	RMS Jitter at 3 MHz	-	156	-	ps	
SID228	T <sub>JITRMSIMO2</sub>	RMS Jitter at 24 MHz	-	145	-	ps	
SID229	T <sub>JITRMSIMO3</sub>	RMS Jitter at 48 MHz	-	139	-	ps	

Internal Low-Speed Oscillator

## Table 35. ILO DC Specifications

(Guaranteed by Design)

Spec ID	Parameter	Description	Min	Тур	Max	Units	Details/Conditions
SID231	I <sub>ILO1</sub>	ILO operating current at 32 kHz	-	0.3	1.05	μA	Guaranteed by Characterization
SID233	I <sub>ILOLEAK</sub>	ILO leakage current	-	2	15	nA	Guaranteed by Design



# Packaging

The description of the PSoC4200M package dimensions follows.

Spec ID#	Package	Description	Package Dwg #
PKG_1	68-pin QFN	68-pin QFN, 8 mm x 8 mm x 1.0 mm height with 0.4 mm pitch	001-09618
PKG_2	64-pin TQFP	64-pin TQFP, 10 mm x10 mm x 1.4 mm height with 0.5 mm pitch	51-85051
PKG_4	64-pin TQFP	64-pin TQFP, 14 mm x14 mm x 1.4 mm height with 0.8 mm pitch	51-85046
PKG_5	48-pin TQFP	48-pin TQFP, 7 mm x 7 mm x 1.4 mm height with 0.5 mm pitch	51-85135
PKG_6	44-pin TQFP	44-pin TQFP, 10 mm x 10 mm x 1.4 mm height with 0.8 mm pitch	51-85064

## Table 43. Package Characteristics

Parameter	Description	Conditions	Min	Тур	Max	Units
T <sub>A</sub>	Operating ambient temperature		-40	25	85	°C
TJ	Operating junction temperature		-40		100	°C
T <sub>JA</sub>	Package θ <sub>JA</sub> (68-pin QFN)		-	16.8	-	°C/Watt
T <sub>JC</sub>	Package $\theta_{JC}$ (68-pin QFN)		-	2.9	-	°C/Watt
T <sub>JA</sub>	Package θ <sub>JA</sub> (64-pin TQFP, 0.5-mm pitch)		-	56	-	°C/Watt
T <sub>JC</sub>	Package θ <sub>JC</sub> (64-pin TQFP, 0.5-mm pitch)		-	19.5	-	°C/Watt
T <sub>JA</sub>	Package θ <sub>JA</sub> (64-pin TQFP, 0.8-mm pitch)		-	66.4	-	°C/Watt
T <sub>JC</sub>	Package $\theta_{JC}$ (64-pin TQFP, 0.8-mm pitch)		-	18.2	-	°C/Watt
T <sub>JA</sub>	Package θ <sub>JA</sub> (48-pin TQFP, 0.5-mm pitch)		-	67.3	-	°C/Watt
T <sub>JC</sub>	Package θ <sub>JC</sub> (48-pin TQFP, 0.5-mm pitch)		-	30.4	-	°C/Watt
T <sub>JA</sub>	Package θ <sub>JA</sub> (44-pin TQFP, 0.8-mm pitch)		-	57	-	°C/Watt
T <sub>JC</sub>	Package $\theta_{JC}$ (44-pin TQFP, 0.8-mm pitch)		-	25.9	-	°C/Watt

## Table 44. Solder Reflow Peak Temperature

Package	Maximum Peak Temperature	Maximum Time at Peak Temperature
All packages	260 °C	30 seconds

#### Table 45. Package Moisture Sensitivity Level (MSL), IPC/JEDEC J-STD-2

Package	MSL
All packages	MSL 3



# Acronyms

## Table 46. Acronyms Used in this Document

Acronym	Description
abus	analog local bus
ADC	analog-to-digital converter
AG	analog global
АНВ	AMBA (advanced microcontroller bus archi- tecture) high-performance bus, an ARM data transfer bus
ALU	arithmetic logic unit
AMUXBUS	analog multiplexer bus
API	application programming interface
APSR	application program status register
ARM®	advanced RISC machine, a CPU architecture
ATM	automatic thump mode
BW	bandwidth
CAN	Controller Area Network, a communications protocol
CMRR	common-mode rejection ratio
CPU	central processing unit
CRC	cyclic redundancy check, an error-checking protocol
DAC	digital-to-analog converter, see also IDAC, VDAC
DFB	digital filter block
DIO	digital input/output, GPIO with only digital capabilities, no analog. See GPIO.
DMIPS	Dhrystone million instructions per second
DMA	direct memory access, see also TD
DNL	differential nonlinearity, see also INL
DNU	do not use
DR	port write data registers
DSI	digital system interconnect
DWT	data watchpoint and trace
ECC	error correcting code
ECO	external crystal oscillator
EEPROM	electrically erasable programmable read-only memory
EMI	electromagnetic interference
EMIF	external memory interface
EOC	end of conversion
EOF	end of frame
EPSR	execution program status register
ESD	electrostatic discharge

Table 46. Acronyms Used in this Document (continu	ied)
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Acronym	Description
ETM	embedded trace macrocell
FIR	finite impulse response, see also IIR
FPB	flash patch and breakpoint
FS	full-speed
GPIO	general-purpose input/output, applies to a PSoC pin
HVI	high-voltage interrupt, see also LVI, LVD
IC	integrated circuit
IDAC	current DAC, see also DAC, VDAC
IDE	integrated development environment
I <sup>2</sup> C, or IIC	Inter-Integrated Circuit, a communications protocol
lir	infinite impulse response, see also FIR
ILO	internal low-speed oscillator, see also IMO
IMO	internal main oscillator, see also ILO
INL	integral nonlinearity, see also DNL
I/O	input/output, see also GPIO, DIO, SIO, USBIO
IPOR	initial power-on reset
IPSR	interrupt program status register
IRQ	interrupt request
ITM	instrumentation trace macrocell
LCD	liquid crystal display
LIN	Local Interconnect Network, a communications protocol.
LR	link register
LUT	lookup table
LVD	low-voltage detect, see also LVI
LVI	low-voltage interrupt, see also HVI
LVTTL	low-voltage transistor-transistor logic
MAC	multiply-accumulate
MCU	microcontroller unit
MISO	master-in slave-out
NC	no connect
NMI	nonmaskable interrupt
NRZ	non-return-to-zero
NVIC	nested vectored interrupt controller
NVL	nonvolatile latch, see also WOL
opamp	operational amplifier
PAL	programmable array logic, see also PLD
PC	program counter
РСВ	printed circuit board



## Table 46. Acronyms Used in this Document (continued)

Acronym	Description
PGA	programmable gain amplifier
PHUB	peripheral hub
PHY	physical layer
PICU	port interrupt control unit
PLA	programmable logic array
PLD	programmable logic device, see also PAL
PLL	phase-locked loop
PMDD	package material declaration data sheet
POR	power-on reset
PRES	precise power-on reset
PRS	pseudo random sequence
PS	port read data register
PSoC <sup>®</sup>	Programmable System-on-Chip™
PSRR	power supply rejection ratio
PWM	pulse-width modulator
RAM	random-access memory
RISC	reduced-instruction-set computing
RMS	root-mean-square
RTC	real-time clock
RTL	register transfer language
RTR	remote transmission request
RX	receive
SAR	successive approximation register
SC/CT	switched capacitor/continuous time
SCL	I <sup>2</sup> C serial clock
SDA	I <sup>2</sup> C serial data
S/H	sample and hold
SINAD	signal to noise and distortion ratio
SIO	special input/output, GPIO with advanced features. See GPIO.
SOC	start of conversion
SOF	start of frame
SPI	Serial Peripheral Interface, a communications protocol
SR	slew rate
SRAM	static random access memory
SRES	software reset
SWD	serial wire debug, a test protocol
SWV	single-wire viewer
TD	transaction descriptor, see also DMA

#### Table 46. Acronyms Used in this Document (continued)

Acronym	Description
THD	total harmonic distortion
TIA	transimpedance amplifier
TRM	technical reference manual
TTL	transistor-transistor logic
ТΧ	transmit
UART	Universal Asynchronous Transmitter Receiver, a communications protocol
UDB	universal digital block
USB	Universal Serial Bus
USBIO	USB input/output, PSoC pins used to connect to a USB port
VDAC	voltage DAC, see also DAC, IDAC
WDT	watchdog timer
WOL	write once latch, see also NVL
WRES	watchdog timer reset
XRES	external reset I/O pin
XTAL	crystal